

WHAT IS CLAIMED IS:

1. A plasma etching treatment apparatus comprising:
 - an etching treatment room;
 - a substrate stage for placing a semiconductor substrate thereon installed in the etching treatment room;
 - a plasma generating means for generating plasma in the etching treatment room;
 - a gas introducing means for introducing (a) a treating gas for etching and (b) a treating gas for decomposing and removing etching products, into the etching treatment room; and
 - a monitoring means for monitoring a retained amount of etching products.

2. A plasma etching treatment apparatus comprising:
 - an etching treatment room;
 - a substrate stage, for placing a semiconductor substrate thereon, installed in the etching treatment room;
 - a plasma generating means for generating plasma in the etching treatment room; and
 - a gas introducing means for introducing a treating gas into the etching treatment room.